Product Summary

BV_{DSS}	$R_{DS(ON)}$ Max	I_D Max T_A = +25°C
12V	6.0mΩ @ V_{GS} = 4.5V	14.7A
	9.0mΩ @ V_{GS} = 2.5V	12A

Description

This new generation MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$) yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- General Purpose Interfacing Switch
- Power Management Functions

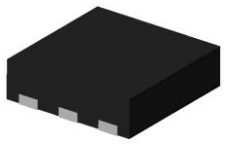
Features

- 0.6mm Profile – Ideal for Low-Profile Applications
- PCB Footprint of 4mm^2
- Low Gate Threshold Voltage
- Low On-Resistance
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative. https://www.diodes.com/quality/product-definitions/**

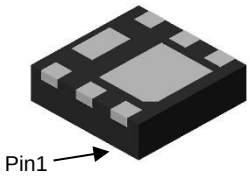
Mechanical Data

- Case: U-DFN2020-6
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – NiPdAu over Copper Leadframe; Solderable per MIL-STD-202, Method 208 e4
- Weight: 0.007 grams (Approximate)

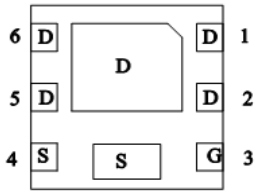
U-DFN2020-6 (Type F)



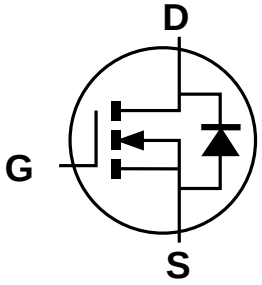
Top View



Bottom View



Pin Out
Bottom View



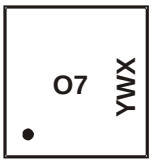
Equivalent Circuit

Ordering Information (Note 4)

Part Number	Case	Packaging
DMN14M8UFDF-7	U-DFN2020-6 (Type F)	3,000/Tape & Reel
DMN14M8UFDF-13	U-DFN2020-6 (Type F)	10,000/Tape & Reel

Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



O7 = Product Type Marking Code
YWX = Date Code Marking
Y = Year (ex: 1 = 2021)
W = Week (ex: a = Week 27; z Represents Week 52 and 53)
X = Internal Code (ex: U = Monday)

Date Code Key

Year	2019	2020	2021	2022	2023	2024	2025	2026	2027	2028	2029	2030
Code	9	0	1	2	3	4	5	6	7	8	9	0

Week	1-26	27-52	53
Code	A-Z	a-z	z

Internal Code	Sun	Mon	Tue	Wed	Thu	Fri	Sat
Code	T	U	V	W	X	Y	Z

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	12	V
Gate-Source Voltage			V_{GSS}	±8	V
Continuous Drain Current (Note 6) V_{GS} = 4.5V	Steady State	T_A = +25°C T_A = +70°C	I_D	14.7 11.8	A
Pulsed Drain Current (380µs Pulse, Duty Cycle = 1%)			I_{DM}	100	A
Maximum Body Diode Continuous Current (Note 6)			I_S	1.7	A
Avalanche Current (Note 7) L = 0.1mH			I_{AS}	5.6	A
Avalanche Energy (Note 7) L = 0.1mH			E_{AS}	1.6	mJ

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T_A = +25°C	P_D	1.1	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	109.5	°C/W
Total Power Dissipation (Note 6)	T_A = +25°C	P_D	1.9	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	63.8	°C/W
Thermal Resistance, Junction to Case (Note 6)		$R_{\theta JC}$	9	
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV_{DSS}	12	—	—	V	V_{GS} = 0V, I_D = 250µA
Zero Gate Voltage Drain Current T_J = +25°C	I_{DSS}	—	—	1	µA	V_{DS} = 9.6V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±100	nA	V_{GS} = ±8V, V_{DS} = 0V
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	$V_{GS(TH)}$	0.45	—	1.2	V	V_{DS} = V_{GS}, I_D = 250µA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	4.8	6.0	mΩ	V_{GS} = 4.5V, I_D = 12A
		—	6.1	9.0		V_{GS} = 2.5V, I_D = 10A
Diode Forward Voltage	V_{SD}	—	0.69	1.2	V	V_{GS} = 0V, I_S = 3.2A
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C_{iss}	—	1246	—	pF	V_{DS} = 6V, V_{GS} = 0V, f = 1.0MHz
Output Capacitance	C_{oss}	—	454	—	pF	
Reverse Transfer Capacitance	C_{rss}	—	352	—	pF	
Gate Resistance	R_G	—	5	—	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1MHz
Total Gate Charge (V_{GS} = 4.5V)	Q_g	—	14.6	—	nC	V_{DS} = 6V, I_D = 10A
Total Gate Charge (V_{GS} = 10V)	Q_g	—	29.5	—	nC	
Gate-Source Charge	Q_{gs}	—	1.2	—	nC	
Gate-Drain Charge	Q_{gd}	—	4.9	—	nC	
Turn-On Delay Time	$t_{D(ON)}$	—	4.7	—	ns	V_{DS} = 6V, I_D = 5.0A V_{GS} = 4.5V, R_G = 1.0Ω
Turn-On Rise Time	t_R	—	5	—	ns	
Turn-Off Delay Time	$t_{D(OFF)}$	—	36.6	—	ns	
Turn-Off Fall Time	t_F	—	19	—	ns	
Reverse Recovery Time	t_{RR}	—	24.5	—	ns	I_F = 2.0A, di/dt = 100A/µs
Reverse Recovery Charge	Q_{RR}	—	7	—	nC	

Notes:
5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1-inch square copper plate.
7. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C.
8. Short duration pulse test used to minimize self-heating effect.
9. Guaranteed by design. Not subject to product testing.

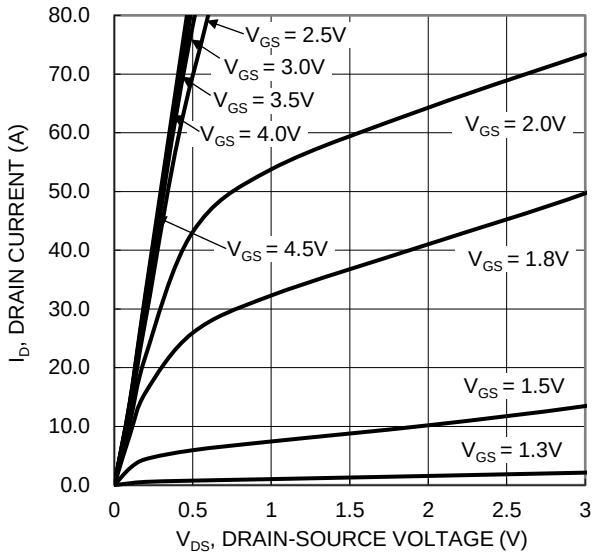


Figure 1. Typical Output Characteristic

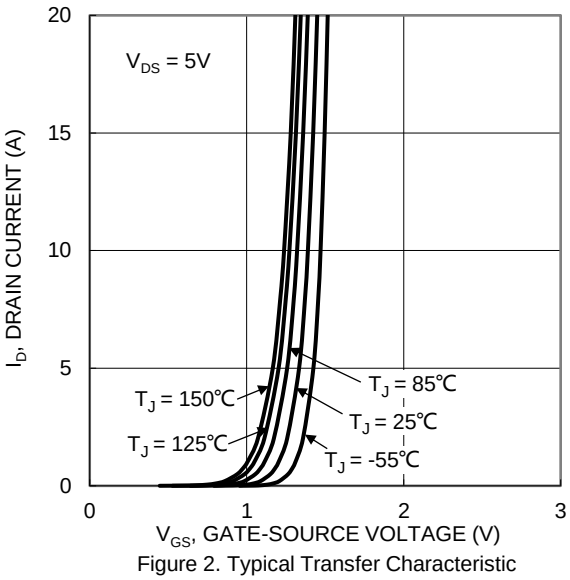


Figure 2. Typical Transfer Characteristic

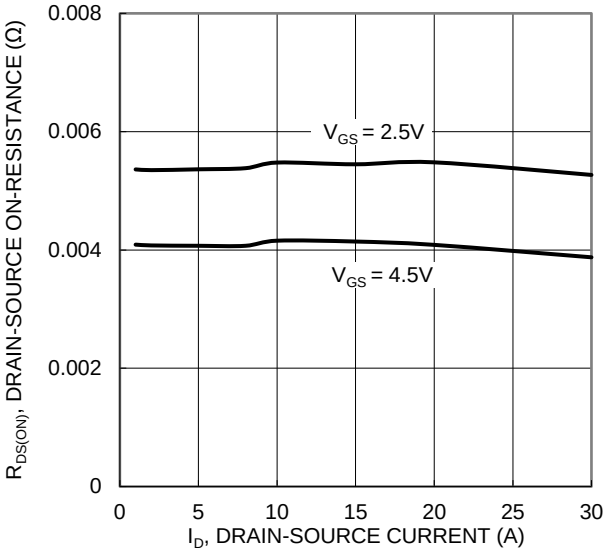


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

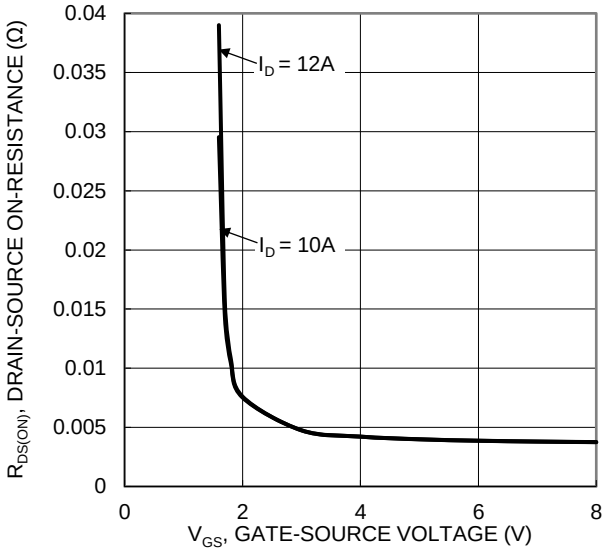


Figure 4. Typical Transfer Characteristic

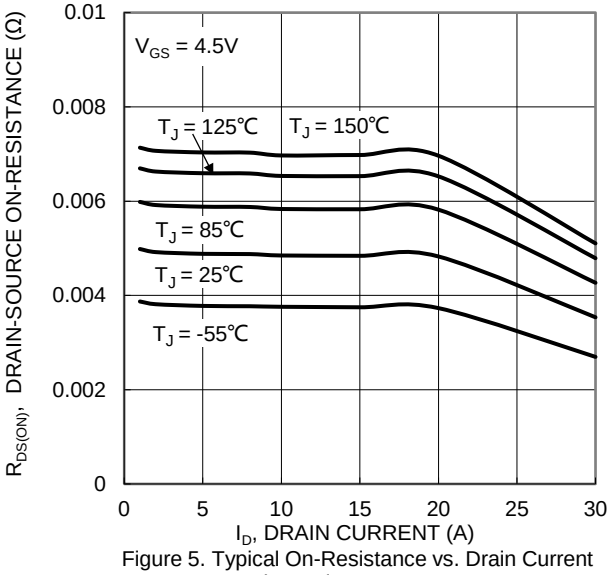


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

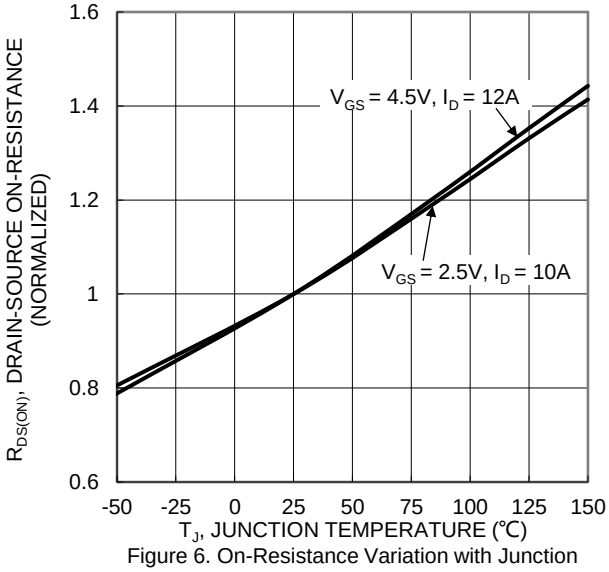


Figure 6. On-Resistance Variation with Junction Temperature

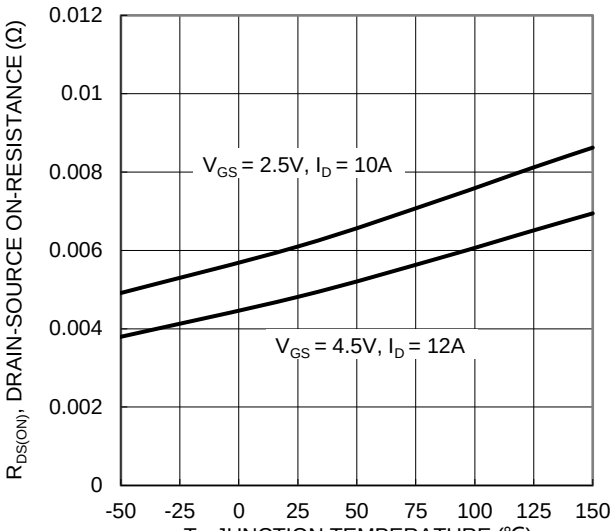


Figure 7. On-Resistance Variation with Junction Temperature

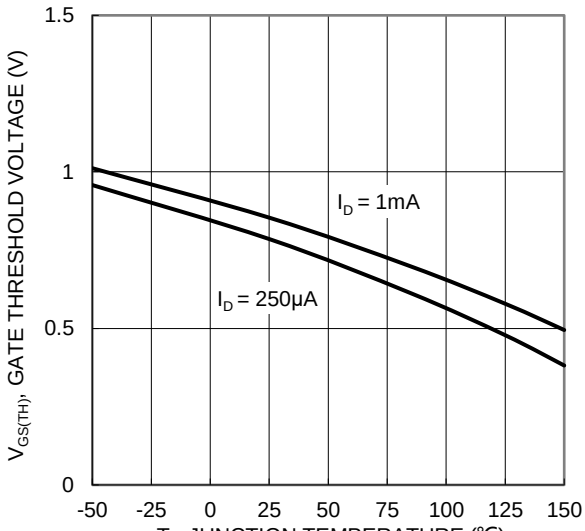


Figure 8. Gate Threshold Variation vs. Junction Temperature

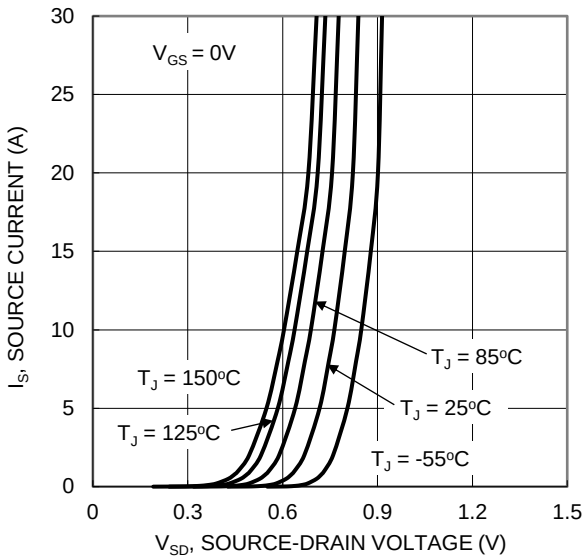


Figure 9. Diode Forward Voltage vs. Current

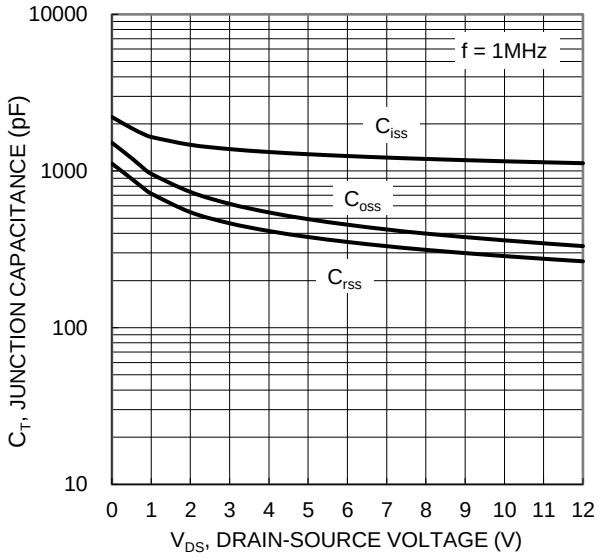


Figure 10. Typical Junction Capacitance

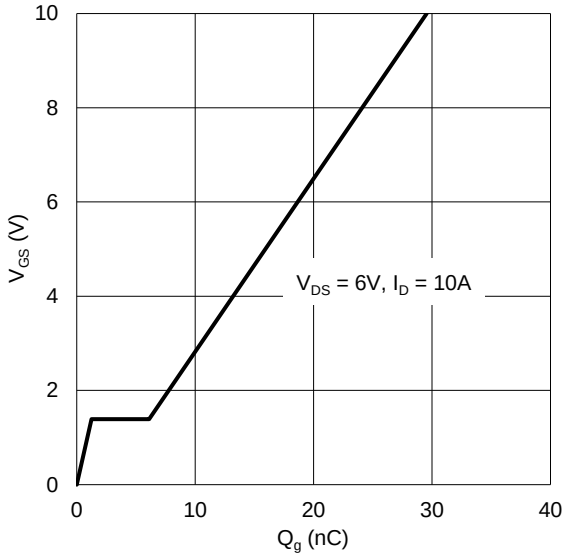


Figure 11. Gate Charge

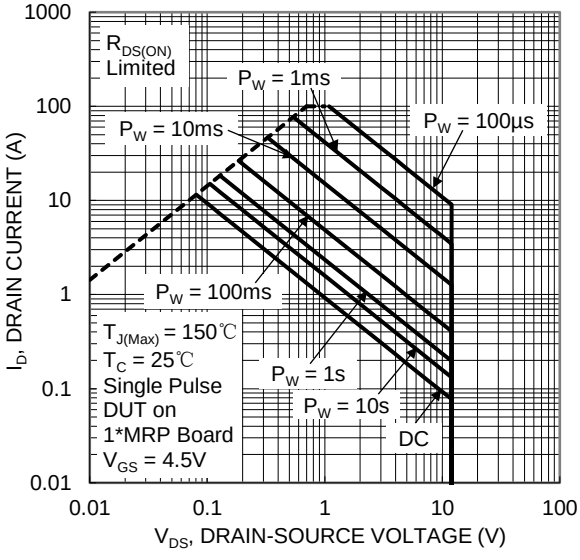


Figure 12. SOA, Safe Operation Area

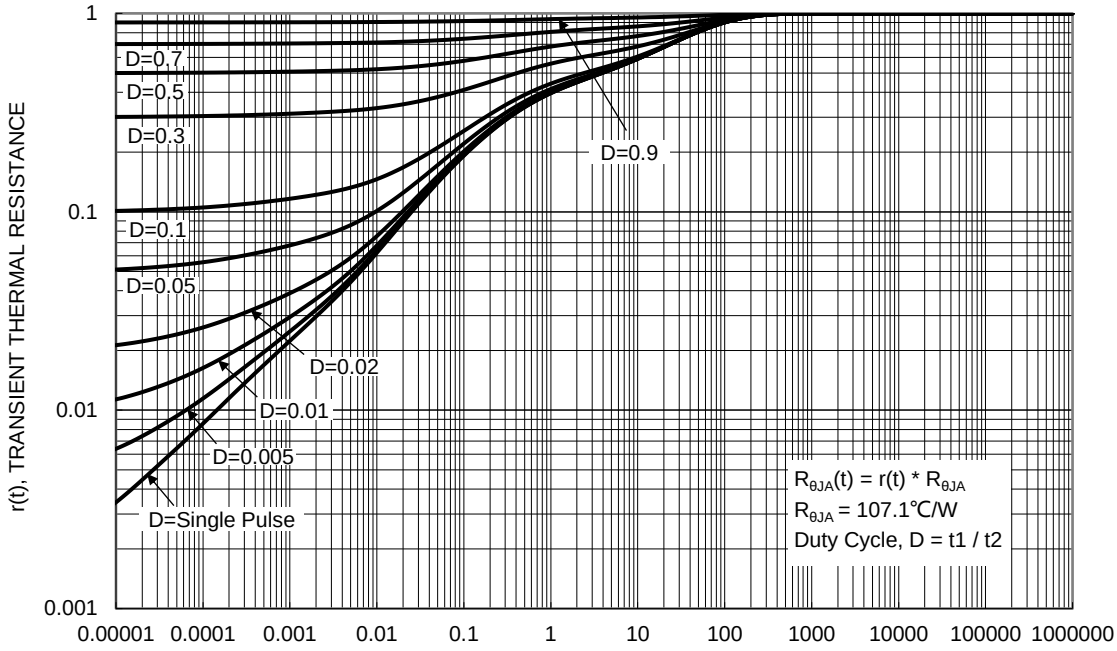
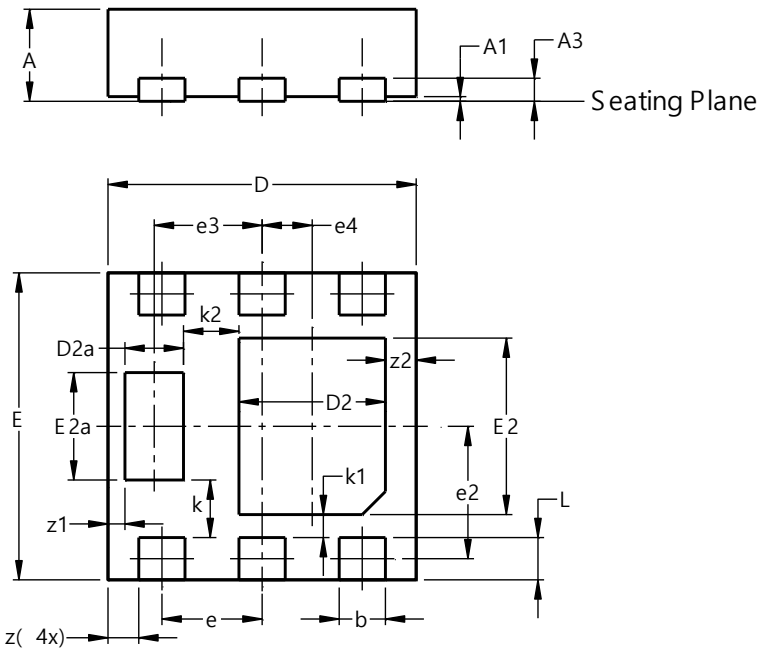


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-DFN2020-6 (Type F)

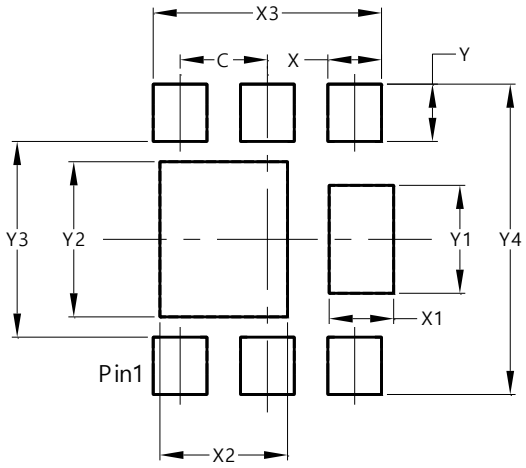


U-DFN2020-6 (Type F)			
Dim	**Min**	**Max**	**Typ**
A	0.57	0.63	0.60
A1	0.00	0.05	0.03
A3	-	-	0.15
b	0.25	0.35	0.30
D	1.95	2.05	2.00
D2	0.85	1.05	0.95
D2a	0.33	0.43	0.38
E	1.95	2.05	2.00
E2	1.05	1.25	1.15
E2a	0.65	0.75	0.70
e	0.65 BSC		
e2	0.863 BSC		
e3	0.70 BSC		
e4	0.325 BSC		
k	0.37 BSC		
k1	0.15 BSC		
k2	0.36 BSC		
L	0.225	0.325	0.275
z	0.20 BSC		
z1	0.110 BSC		
z2	0.20 BSC		
All Dimensions in mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-DFN2020-6 (Type F)



Dimensions	Value (in mm)
C	0.650
X	0.400
X1	0.480
X2	0.950
X3	1.700
Y	0.425
Y1	0.800
Y2	1.150
Y3	1.450
Y4	2.300

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